

GMBD3004\A\C\S**SURFACE MOUNT, SWITCHING DIODE****VOLTAGE 350V, CURRENT 0.225A****Description**

The GMBD3004\A\C\S are designed for ultra high speed switching.

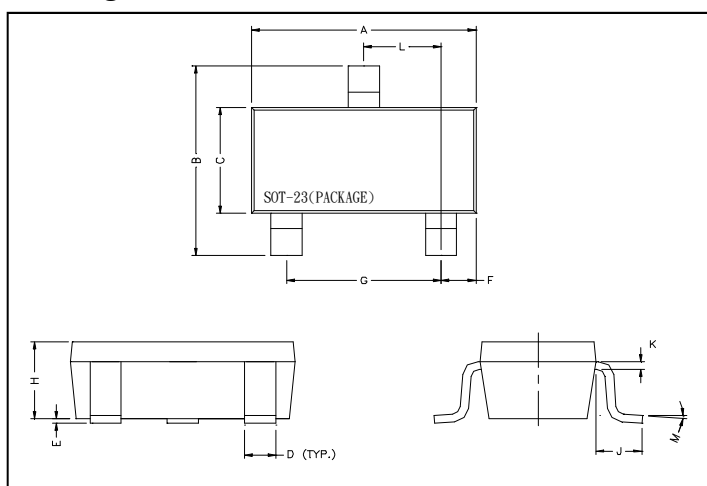
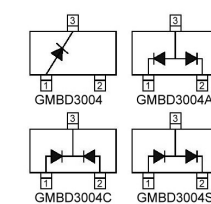
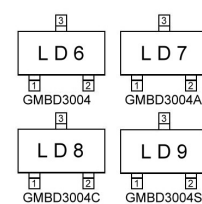
Package Dimensions

Diagram:



Marking:



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings (At $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Max. Repetitive Peak Reverse Voltage	V_{RRM}	350	V
Max. RMS Voltage	V_{RMS}	212	V
Max. DC Blocking Voltage	V_{DC}	300	V
Max. Average Forward Rectified Current	I_O	225	mA
Non-Repetitive Peak Forward surge Current @ $T_p = 1.0\mu\text{s}$ @ $T_p = 1.0\text{s}$	IFSM	4	A
		1	
Typical Junction Capacitance between Terminal (Note1)	C_J	5.0	pF
Max. Reverse Recovery Time (Note2)	T_{RR}	50	nSec
Power Dissipation	PD	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Operation and Storage Temperature Range	T_J, T_{STG}	-65 ~ +150	$^\circ\text{C}$

Electrical Characteristics (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

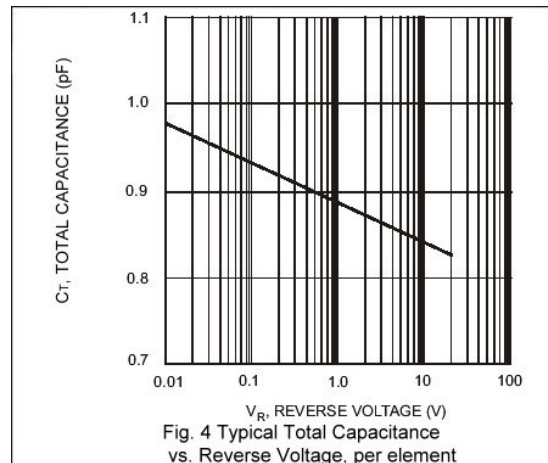
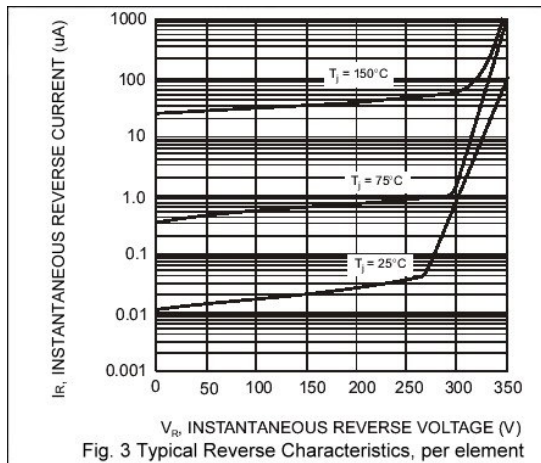
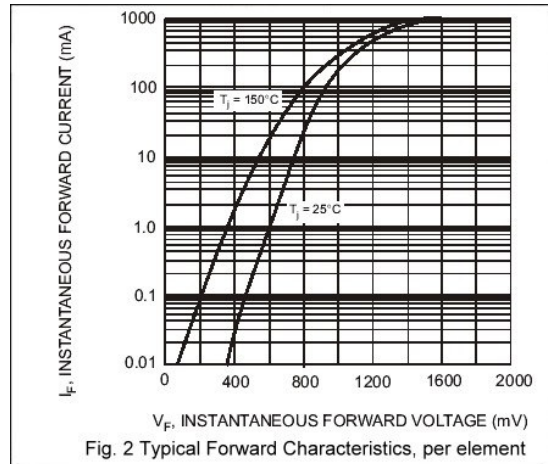
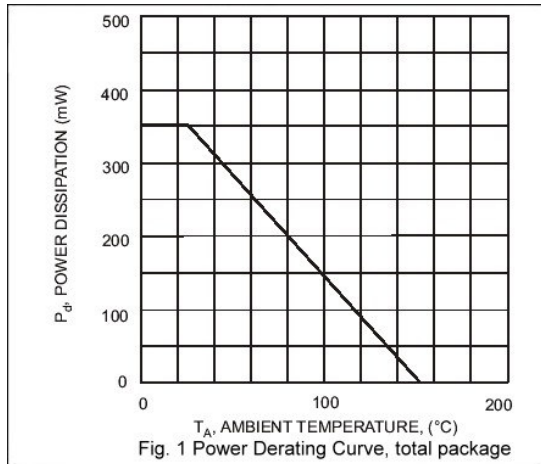
Characteristics	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	BV_R	350	-	V	$I_R = 150\mu\text{A}$
Max. instantaneous Forward Voltage	V_F	-	1.0	V	$I_F = 100\text{mA}$
Max. Average Reverse Current	I_R	-	100	nA	$V_R = 240\text{V}, T_A = 25^\circ\text{C}$
			100	μA	$V_R = 240\text{V}, T_A = 150^\circ\text{C}$

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.

2. Measured at applied forward current of 30mA, reverse current of 30mA, $R_L = 100\Omega$ and recovery to $I_{RR} = -3\text{mA}$.

3. ESD sensitive product handling required.

Characteristics Curve

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